

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/661,038	09/12/2003	Cheng T. Horng	HT03-006	6707
7590 07/19/2006		EXAMINER		
STEPHEN B. ACKERMAN 28 DAVIS AVENUE			MCDONALD, RODNEY GLENN	
POUGHKEEPSIE, NY 12603			ART UNIT PAPER NUMBE	
	,		1753	

DATE MAILED: 07/19/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

		<i>D</i>				
	Application No.	Applicant(s)				
	10/661,038	HORNG ET AL.				
Office Action Summary	Examiner	Art Unit				
	Rodney G. McDonald	1753				
The MAILING DATE of this communication app Period for Reply	ears on the cover sneet with the c	orrespondence address				
A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DA - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period w - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be timudil apply and will expire SIX (6) MONTHS from a cause the application to become ABANDONE	N. nely filed the mailing date of this communication. D (35 U.S.C. § 133).				
Status						
1) Responsive to communication(s) filed on 18 Ap	oril 2006.					
2a) This action is FINAL . 2b) ⊠ This	action is non-final.					
•	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.					
Disposition of Claims						
4) ☐ Claim(s) 1-21 is/are pending in the application. 4a) Of the above claim(s) 13-21 is/are withdraw 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1-12 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or	n from consideration.					
Application Papers						
9) The specification is objected to by the Examine						
10) The drawing(s) filed on is/are: a) acceed applicant may not request that any objection to the						
Replacement drawing sheet(s) including the correcti	-····					
11) The oath or declaration is objected to by the Ex		• •				
Priority under 35 U.S.C. § 119						
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the prior application from the International Bureau * See the attached detailed Office action for a list of	s have been received. s have been received in Application ity documents have been received (PCT Rule 17.2(a)).	on No ed in this National Stage				
Attachment(s)	_					
1) Notice of References Cited (PTO-892)	4) 🔲 Interview Summary Paper No(s)/Mail Da	(PTO-413)				
 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 12/2003, 3/2006. 		atent Application (PTO-152)				

Application/Control Number: 10/661,038

Art Unit: 1753

DETAILED ACTION

Election/Restrictions

Applicant's election with traverse of Group I, claims 1-12 in the reply filed on May 9, 2006 is acknowledged. The traversal is on the ground(s) that the process claims necessarily use the product and vice versa and therefore the field of search must necessarily cover both the product and process. This is not found persuasive because the product can be made by another and materially different process such as utilizing another process such CVD instead of "using an ultra-low pressure Ar/O₂ mixture as a sputtering gas".

The requirement is still deemed proper and is therefore made FINAL.

Claim Rejections - 35 USC § 112

Claims 1-12 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Claim 1, line 1, is indefinite because the phrase "ultra-thin" lacks basis for comparison.

Claim 1, line 2, is indefinite because "high" lacks basis for comparison.

Claim 1, lines 4, 5, 11, 14, 16, 18, is indefinite because "ultra-low" lacks basis for comparison.

Claim 3, lines 1, 2, is indefinite because "ultra-low" lacks basis for comparison.

Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

Hoshiya et al. (U.S. PGPUB 2002/0041473) and Kula et al. (U.S. PGPUB 2003/0021071) teach spin valve sensors but fail to teach forming the spin valve GMR sensor element as claimed by applicant including the specifics for depositing the layers in the sputtering chamber.

Allowable Subject Matter

Claims 1-12 would be allowable if rewritten or amended to overcome the rejection(s) under 35 U.S.C. 112, 2nd paragraph, set forth in this Office action.

The following is a statement of reasons for the indication of allowable subject matter:

Claims 1-12 are indicated as being allowable over the prior art of record because the prior art of record does not teach a method for forming a spin valve GMR sensor element with layers having sub-atomic monolayers of oxygen absorbed on the surfaces thereof comprising providing, in an ultra-low base pressure sputtering chamber, a substrate; forming on the substrate, using an ultra-low pressure Ar/O₂ mixture as a sputtering gas, a seed layer; forming, using said sputtering gas, an antiferromagnetic pinning layer on the seed layer; forming, using the sputtering gas, a synthetic antiferromagnetic (SyAF) pinned layer formed on the pinning layer; forming, using only ultra-low pressure Ar as a sputtering gas, a Cu spacer layer on the SyAF layer, the surface of the spacer layer not contacting the SyAF layer then being treated with O₂ to

Page 4

form an oxygen surfactant layer (OSL); forming, again using the ultra-low pressure Ar/O₂, a ferromagnetic free layer on the OSL of the treated spacer layer; forming, using only ultra-low pressure Ar as a sputtering gas, a Ru capping layer on the ferromagnetic free layer, then forming an OSL layer on the Ru layer; forming, using the ultra-low

pressure Ar/O₂ mixture as a sputtering gas, a Ta capping layer on the Ru capping layer. Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Rodney G. McDonald whose telephone number is 571-

272-1340. The examiner can normally be reached on M- Th with Every other Friday off.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nam X. Nguyen can be reached on 571-272-1342. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

> Rodnev G. McDonald **Primary Examiner**

Art Unit 1753

July 11, 2006